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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e500v2
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	800MHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 90°C (TA)
Security Features	-
Package / Case	783-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc8533vtang

  - Two key (K1, K2, K1) or three key (K1, K2, K3)
  - ECB and CBC modes for both DES and 3DES
- AESU—Advanced Encryption Standard unit
  - Implements the Rijndael symmetric key cipher
  - ECB, CBC, CTR, and CCM modes
  - 128-, 192-, and 256-bit key lengths
- AFEU—ARC four execution unit
  - Implements a stream cipher compatible with the RC4 algorithm
  - 40- to 128-bit programmable key
- MDEU—message digest execution unit
  - SHA with 160- or 256-bit message digest
  - MD5 with 128-bit message digest
  - HMAC with either algorithm
- KEU—Kasumi execution unit
  - Implements F8 algorithm for encryption and F9 algorithm for integrity checking
  - Also supports A5/3 and GEA-3 algorithms
- RNG—random number generator
- XOR engine for parity checking in RAID storage applications

- Dual I^2C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data bus operating at up to 133 MHz
  - Eight chip selects support eight external slaves
  - Up to eight-beat burst transfers
  - The 32-, 16-, and 8-bit port sizes are controlled by an on-chip memory controller.
  - Two protocol engines available on a per chip select basis:

Table 1. Absolute Maximum Ratings[1] (continued)

Characteristic		Symbol	Max Value	Unit	Notes
DDR and DDR2 DRAM I/O voltage		GV_{DD}	–0.3 to 2.75 –0.3 to 1.98	V	—
Three-speed Ethernet I/O, MII management voltage		LV_{DD} (eTSEC1)	–0.3 to 3.63 –0.3 to 2.75	V	—
		TV_{DD} (eTSEC3)	–0.3 to 3.63 –0.3 to 2.75	V	—
PCI, DUART, system control and power management, I^2C, and JTAG I/O voltage		OV_{DD}	–0.3 to 3.63	V	—
Local bus I/O voltage		BV_{DD}	–0.3 to 3.63 –0.3 to 2.75 –0.3 to 1.98	V	—
Input voltage	DDR/DDR2 DRAM signals	MV_{IN}	–0.3 to (GV_{DD} + 0.3)	V	2
	DDR/DDR2 DRAM reference	MV_{REF}	–0.3 to (GV_{DD} + 0.3)	V	2
	Three-speed Ethernet signals	LV_{IN} TV_{IN}	–0.3 to (LV_{DD} + 0.3) –0.3 to (TV_{DD} + 0.3)	V	2
	Local bus signals	BV_{IN}	–0.3 to (BV_{DD} + 0.3)	V	—
	DUART, SYSCLK, system control and power management, I^2C, and JTAG signals	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	2
	PCI	OV_{IN}	–0.3 to (OV_{DD} + 0.3)	V	2
Storage temperature range		T_{STG}	–55 to 150	°C	—

Notes:
1. Functional and tested operating conditions are given in Table 2. Absolute maximum ratings are stress ratings only, and functional operation at the maximums is not guaranteed. Stresses beyond those listed may affect device reliability or cause.
2. (M,L,O)V_{IN}, and MV_{REF} may overshoot/undershoot to a voltage and for a maximum duration as shown in Figure 2.

2.1.2 Recommended Operating Conditions

Table 2 provides the recommended operating conditions for this device. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Notes
Core supply voltage	V_{DD}	1.0 ± 50 mV	V	—
PLL supply voltage	AV_{DD}	1.0 ± 50 mV	V	1
Core power supply for SerDes transceivers	SV_{DD}	1.0 ± 50 mV	V	—
Pad power supply for SerDes transceivers	XV_{DD}	1.0 ± 50 mV	V	—
DDR and DDR2 DRAM I/O voltage	GV_{DD}	2.5 V ± 125 mV 1.8 V ± 90 mV	V	2

4.2 Real-Time Clock Timing

The RTC input is sampled by the platform clock (CCB clock). The output of the sampling latch is then used as an input to the counters of the PIC and the TimeBase unit of the e500. There is no jitter specification. The minimum pulse width of the RTC signal should be greater than 2 × the period of the CCB clock. That is, minimum clock high time is $2 \times t_{CCB}$, and minimum clock low time is $2 \times t_{CCB}$. There is no minimum RTC frequency; RTC may be grounded if not needed.

4.3 eTSEC Gigabit Reference Clock Timing

Table 7 provides the eTSEC gigabit reference clocks (EC_GTX_CLK125) AC timing specifications for the MPC8533E.

Table 7. EC_GTX_CLK125 AC Timing Specifications

Parameter/Condition	Symbol	Min	Typ	Max	Unit	Notes
EC_GTX_CLK125 frequency	f_{G125}	—	125	—	MHz	—
EC_GTX_CLK125 cycle time	t_{G125}	—	8	—	ns	—
EC_GTX_CLK rise and fall time LV_{DD}, TV_{DD} = 2.5 V LV_{DD}, TV_{DD} = 3.3 V	t_{G125R}/t_{G125F}	—	—	 0.75 1.0	ns	1
EC_GTX_CLK125 duty cycle GMII, TBI 1000Base-T for RGMII, RTBI	t_{G125H}/t_{G125}	 45 47	—	 55 53	%	2

Notes:

1. Rise and fall times for EC_GTX_CLK125 are measured from 0.5 and 2.0 V for L/TV_{DD} = 2.5 V, and from 0.6 and 2.7 V for L/TVDD = 3.3 V.
2. EC_GTX_CLK125 is used to generate the GTX clock for the eTSEC transmitter with 2% degradation. EC_GTX_CLK125 duty cycle can be loosened from 47%/53% as long as the PHY device can tolerate the duty cycle generated by the eTSEC GTX_CLK. See Section 8.5.4, "RGMII and RTBI AC Timing Specifications," for duty cycle for 10Base-T and 100Base-T reference clock.

4.4 Platform to FIFO Restrictions

Please note the following FIFO maximum speed restrictions based on platform speed.

For FIFO GMII mode:

FIFO TX/RX clock frequency ≤ platform clock frequency ÷ 4.2

For example, if the platform frequency is 533 MHz, the FIFO Tx/Rx clock frequency should be no more than 127 MHz.

For FIFO encoded mode:

FIFO TX/RX clock frequency ≤ platform clock frequency ÷ 3.2

For example, if the platform frequency is 533 MHz, the FIFO Tx/Rx clock frequency should be no more than 167 MHz.

Table 12. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Output low current (V_{OUT} = 0.42 V)	I_{OL}	16.2	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.

Table 13 provides the DDR I/O capacitance when GV_{DD}(typ) = 2.5 V.

Table 13. DDR SDRAM Capacitance for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the current draw characteristics for MV_{REF}.

Table 14. Current Draw Characteristics for MV_{REF}

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

Note:
1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 15 provides the input AC timing specifications for the DDR SDRAM when GV_{DD}(typ) = 1.8 V.

Table 15. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.25	V	—
AC input high voltage	V_{IH}	MV_{REF} + 0.25	—	V	—

Table 16 provides the input AC timing specifications for the DDR SDRAM when $GV_{DD}(typ) = 2.5$ V.

Table 16. DDR SDRAM Input AC Timing Specifications for 2.5-V Interface

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	$MV_{REF} - 0.31$	V	—
AC input high voltage	V_{IH}	$MV_{REF} + 0.31$	—	V	—

Table 17 provides the input AC timing specifications for the DDR SDRAM interface.

Table 17. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions.

Parameter	Symbol	Min	Max	Unit	Notes
Controller skew for MDQS—MDQ/MECC/MDM	t_{CISKEW}			ps	1, 2
533 MHz		–300	300		3
400 MHz		–365	365		—
333 MHz		–390	390		—

Notes:

1. t_{CISKEW} represents the total amount of skew consumed by the controller between MDQS[n] and any corresponding bit that will be captured with MDQS[n]. This should be subtracted from the total timing budget.
2. The amount of skew that can be tolerated from MDQS to a corresponding MDQ signal is called t_{DISKEW}. This can be determined by the following equation: $t_{DISKEW} = \pm (T/4 - abs(t_{CISKEW}))$, where T is the clock period and $abs(t_{CISKEW})$ is the absolute value of t_{CISKEW}. See Figure 3.
3. Maximum DDR1 frequency is 400 MHz.

Figure 3 shows the DDR SDRAM input timing diagram.

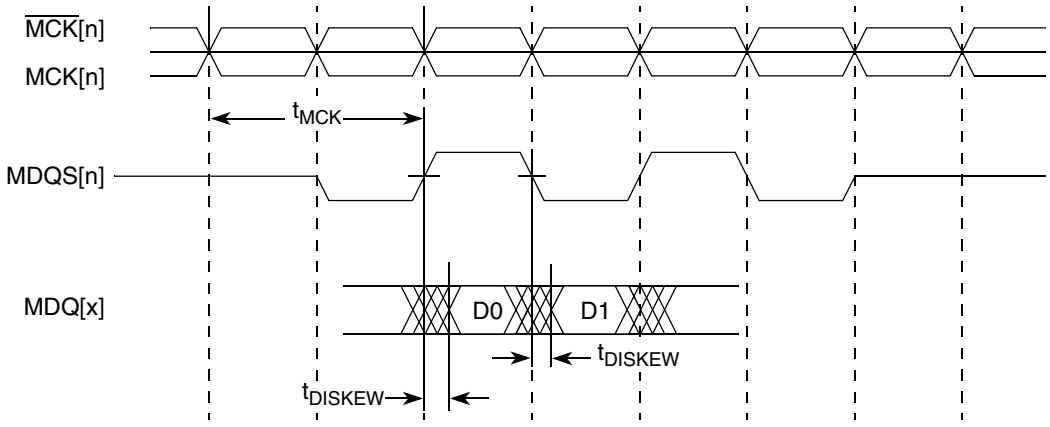

Figure 3. DDR SDRAM Input Timing Diagram (t_{DISKEW})

Table 18. DDR SDRAM Output AC Timing Specifications (continued)

At recommended operating conditions.

Parameter	Symbol[1]	Min	Max	Unit	Notes
MDQS postamble	t_{DDKHME}	0.4 x tMCK	0.6 x tMCK	ns	6

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (AX or DX). For example, t_{DDKHAS} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (A) are setup (S) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.
2. All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.
3. ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$, $\overline{\text{MCS}}$, and MDQ/MECC/MDM/MDQS.
4. Note that t_{DDKHMH} follows the symbol conventions described in note 1. For example, t_{DDKHMH} describes the DDR timing (DD) from the rising edge of the MCK[n] clock (KH) until the MDQS signal is valid (MH). t_{DDKHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. This will typically be set to the same delay as the clock adjust in the CLK_CNTL register. The timing parameters listed in the table assume that these two parameters have been set to the same adjustment value. See the *MPC8533E PowerQUICC III Integrated Communications Processor Reference Manual,* for a description and understanding of the timing modifications enabled by use of these bits.
5. Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the microprocessor.
6. All outputs are referenced to the rising edge of MCK[n] at the pins of the microprocessor. Note that t_{DDKHMP} follows the symbol conventions described in note 1.
7. Maximum DDR1 frequency is 400 MHz.

NOTE

For the ADDR/CMD setup and hold specifications in Table 18, it is assumed that the clock control register is set to adjust the memory clocks by ½ applied cycle.

Figure 4 shows the DDR SDRAM output timing for the MCK to MDQS skew measurement (t_{DDKHMH}).

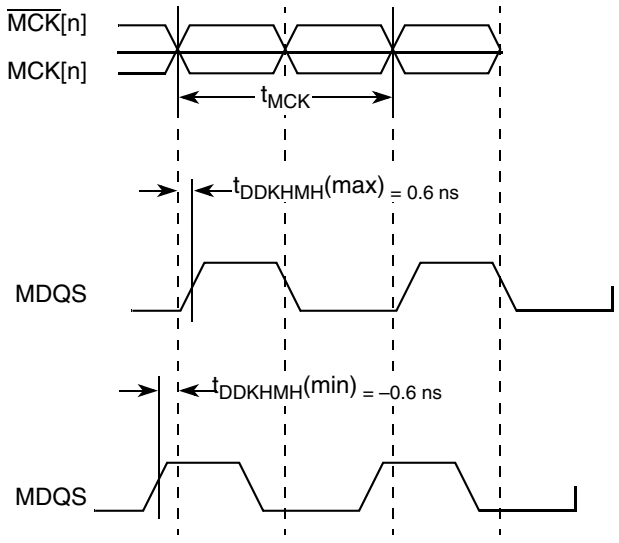

Figure 4. Timing Diagram for t_{DDKHMH}

Figure 5 shows the DDR SDRAM output timing diagram.

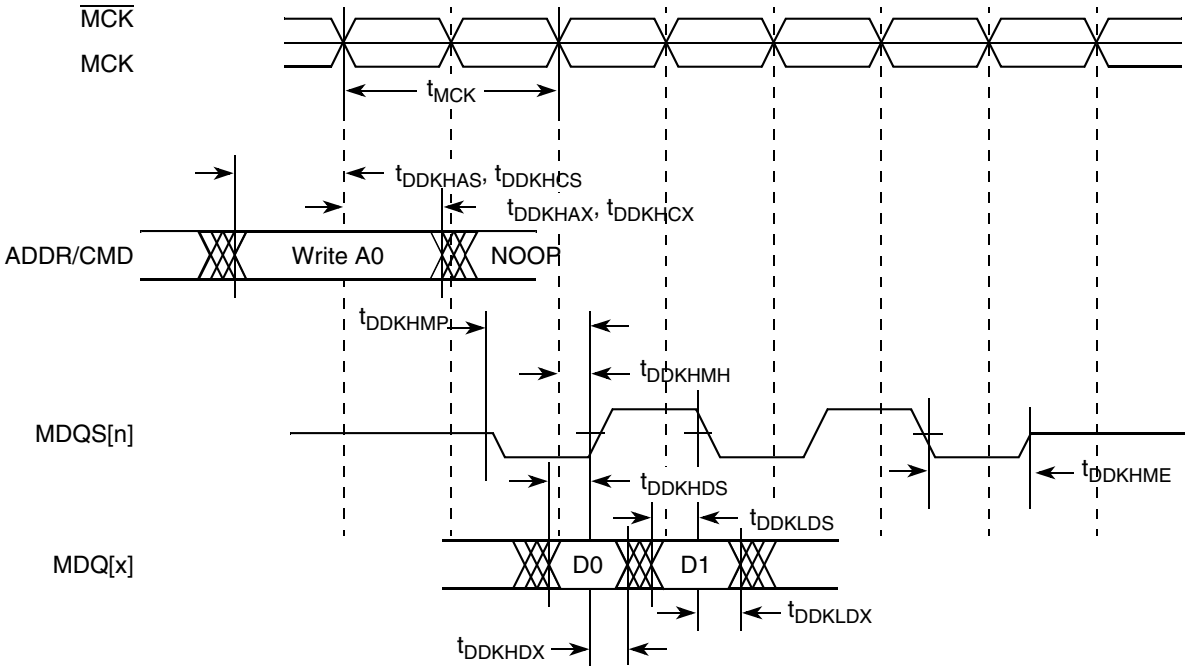

Figure 5. DDR and DDR2 SDRAM Output Timing Diagram

Figure 6 provides the AC test load for the DDR bus.

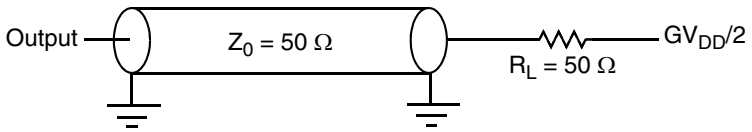

Figure 6. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8533E.

7.1 DUART DC Electrical Characteristics

Table 19 provides the DC electrical characteristics for the DUART interface.

Table 19. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V	—
Low-level input voltage	V_{IL}	–0.3	0.8	V	—
Input current (V_{IN} = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA	1
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	2.4	—	V	—

Table 28. MII Receive AC Timing Specifications (continued)

At recommended operating conditions with L/TVDD of 3.3 V ± 5%.or 2.5 V ± 5%.

Parameter/Condition	Symbol[1]	Min	Typ	Max	Unit	Notes
RXD[3:0], RX_DV, RX_ER setup time to RX_CLK	t_{MRDVKH}	10.0	—	—	ns	—
RXD[3:0], RX_DV, RX_ER hold time to RX_CLK	t_{MRDXKH}	10.0	—	—	ns	—
RX_CLK clock rise (20%–80%)	t_{MRXR}	1.0	—	4.0	ns	—
RX_CLK clock fall time (80%–20%)	t_{MRXF}	1.0	—	4.0	ns	—

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MRDVKH} symbolizes MII receive timing (MR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MRX} clock reference (K) going to the high (H) state or setup time. Also, t_{MRDXKL} symbolizes MII receive timing (GR) with respect to the time data input signals (D) went invalid (X) relative to the t_{MRX} clock reference (K) going to the low (L) state or hold time. Note that, in general, the clock reference symbol representation is based on three letters representing the clock of a particular functional. For example, the subscript of t_{MRX} represents the MII (M) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 13 provides the AC test load for eTSEC.

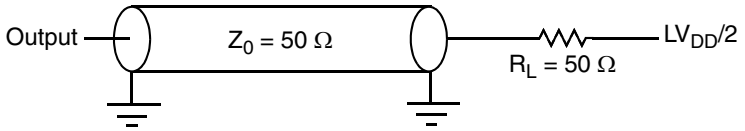

Figure 13. eTSEC AC Test Load

Figure 14 shows the MII receive AC timing diagram.

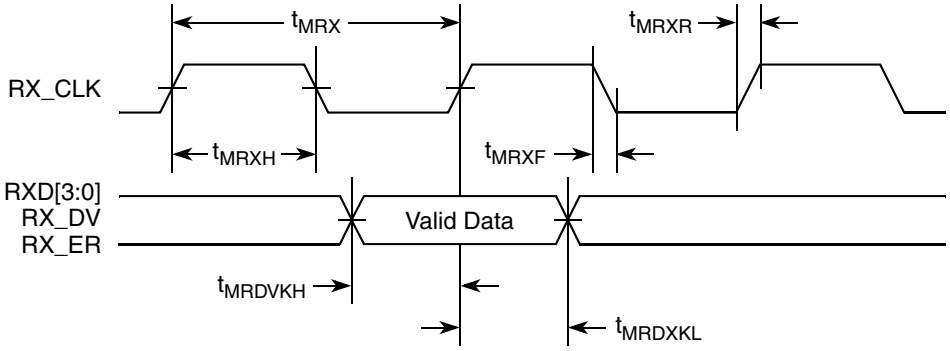

Figure 14. MII Receive AC Timing Diagram

8.5 TBI AC Timing Specifications

This section describes the TBI transmit and receive AC timing specifications.

Figure 34 provides the AC test load for the I^2C.

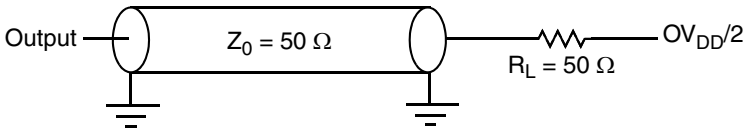

Figure 34. I^2C AC Test Load

Figure 35 shows the AC timing diagram for the I^2C bus.

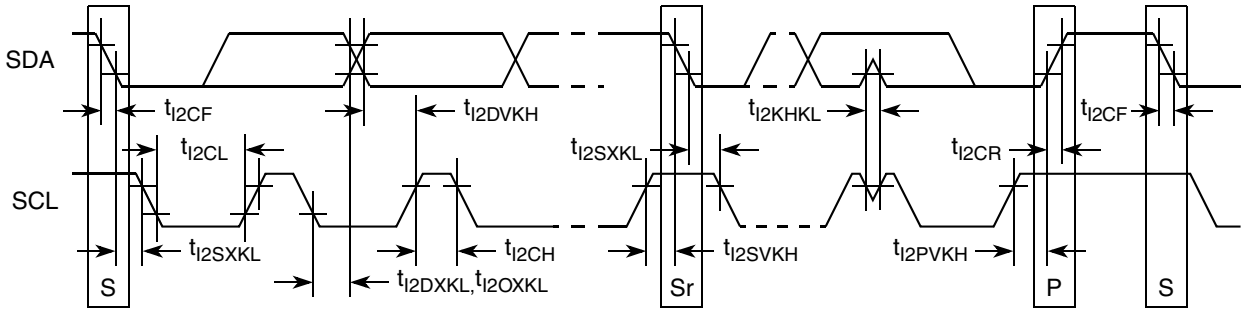

Figure 35. I^2C Bus AC Timing Diagram

14 GPIO

This section describes the DC and AC electrical specifications for the GPIO interface of the MPC8533E.

14.1 GPIO DC Electrical Characteristics

Table 48 provides the DC electrical characteristics for the GPIO interface.

Table 48. GPIO DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V	—
Low-level input voltage	V_{IL}	–0.3	0.8	V	—
Input current (V_{IN} = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA	1
High-level output voltage (OV_{DD} = mn, I_{OH} = –2 mA)	V_{OH}	2.4	—	V	—
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V	—

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

14.2 GPIO AC Electrical Specifications

Table 49 provides the GPIO input and output AC timing specifications.

Table 49. GPIO Input AC Timing Specifications

Parameter	Symbol	Typ	Unit	Notes
GPIO inputs—minimum pulse width	t_{PIWID}	20	ns	1

Note:
1. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

Figure 36 provides the AC test load for the GPIO.

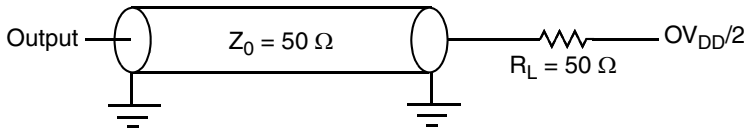

Figure 36. GPIO AC Test Load

15 PCI

This section describes the DC and AC electrical specifications for the PCI bus of the MPC8533E.

15.1 PCI DC Electrical Characteristics

Table 50 provides the DC electrical characteristics for the PCI interface.

Table 50. PCI DC Electrical Characteristics [1]

Parameter	Symbol	Min	Max	Unit	Notes
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V	—
Low-level input voltage	V_{IL}	–0.3	0.8	V	—
Input current (V_{IN} = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA	2
High-level output voltage (OV_{DD} = min, I_{OH} = –2mA)	V_{OH}	2.4	—	V	—
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.4	V	—

Notes:
1. Ranges listed do not meet the full range of the DC specifications of the *PCI 2.2 Local Bus Specifications*.
2. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

— The SerDes reference clock input can be either differential or single-ended. Refer to the differential mode and single-ended mode description below for further detailed requirements.

- The maximum average current requirement that also determines the common mode voltage range:
  — When the SerDes reference clock differential inputs are DC coupled externally with the clock driver chip, the maximum average current allowed for each input pin is 8 mA. In this case, the exact common mode input voltage is not critical as long as it is within the range allowed by the maximum average current of 8 mA (refer to the following bullet for more detail), since the input is AC-coupled on-chip.
  — This current limitation sets the maximum common mode input voltage to be less than 0.4 V (0.4 V/50 = 8 mA) while the minimum common mode input level is 0.1 V above SGND_SRDS*n* (xcorevss). For example, a clock with a 50/50 duty cycle can be produced by a clock driver with output driven by its current source from 0mA to 16mA (0–0.8 V), such that each phase of the differential input has a single-ended swing from 0 V to 800 mV with the common mode voltage at 400 mV.
  — If the device driving the SD*n*_REF_CLK and $\overline{\text{SD}n\text{\_REF\_CLK}}$ inputs cannot drive 50 Ω to SGND_SRDS*n* (xcorevss) DC, or it exceeds the maximum input current limitations, then it must be AC-coupled off-chip.
- The input amplitude requirement
  — This requirement is described in detail in the following sections.

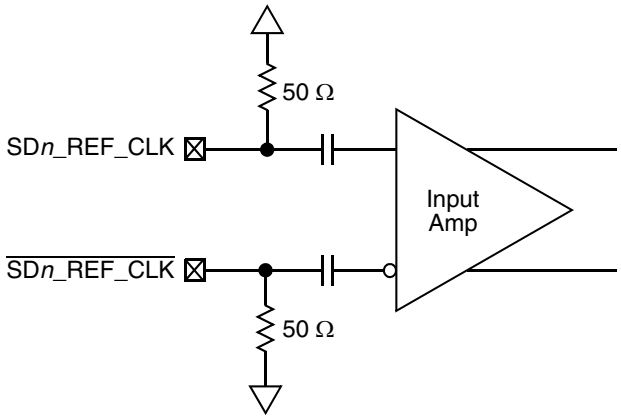

Figure 41. Receiver of SerDes Reference Clocks

16.2.2 DC Level Requirement for SerDes Reference Clocks

The DC level requirement for the MPC8533E SerDes reference clock inputs is different depending on the signaling mode used to connect the clock driver chip and SerDes reference clock inputs as described below.

- **Differential Mode**
  — The input amplitude of the differential clock must be between 400 and 1600 mV differential peak-peak (or between 200 and 800 mV differential peak). In other words, each signal wire of the differential pair must have a single-ended swing less than 800 mV and greater than 200 mV. This requirement is the same for both external DC-coupled or AC-coupled connection.

Table 57. MPC8533E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
SD2_REF_CLK	AF2	I	XV_{DD}	—
SD2_TST_CLK	AG4	—	—	—
SD2_TST_CLK	AF4	—	—	—
General-Purpose Output				
GPOUT[0:7]	AF22, AH23, AG27, AH25, AF21, AF25, AG26, AF26	O	OV_{DD}	—
General-Purpose Input				
GPIN[0:7]	AH24, AG24, AD23, AE21, AD22, AF23, AG25, AE20	I	OV_{DD}	—
System Control				
HRESET	AG16	I	OV_{DD}	—
HRESET_REQ	AG15	O	OV_{DD}	21
SRESET	AG19	I	OV_{DD}	—
CKSTP_IN	AH5	I	OV_{DD}	—
CKSTP_OUT	AA12	O	OV_{DD}	2, 4
Debug				
TRIG_IN	AC5	I	OV_{DD}	—
TRIG_OUT/READY/ QUIESCE	AB5	O	OV_{DD}	5, 8, 15, 21
MSRCID[0:1]	Y7, W9	O	OV_{DD}	4, 5, 8
MSRCID[2:4]	AA9, AB6, AD5	O	OV_{DD}	5, 15, 21
MDVAL	Y8	O	OV_{DD}	5
CLK_OUT	AE16	O	OV_{DD}	10
Clock				
RTC	AF15	I	OV_{DD}	—
SYSCLK	AH16	I	OV_{DD}	—
JTAG				
TCK	AG28	I	OV_{DD}	—
TDI	AH28	I	OV_{DD}	11
TDO	AF28	O	OV_{DD}	10
TMS	AH27	I	OV_{DD}	11
TRST	AH22	I	OV_{DD}	11

Table 57. MPC8533E Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
AVDD_SRDS	W28	Power for SRDSPLL (1.0 V)	—	19
AVDD_SRDS2	AG1	Power for SRDSPLL (1.0 V)	—	19
SENSEVDD	W11	O	V_{DD}	12
SENSEVSS	W10	—	—	12
Analog Signals				
MVREF	A28	Reference voltage signal for DDR	MVREF	—
SD1_IMP_CAL_RX	M26	—	200Ω to GND	—
SD1_IMP_CAL_TX	AE28	—	100Ω to GND	—
SD1_PLL_TPA	V26	—	AVDD_SRDS ANALOG	17
SD2_IMP_CAL_RX	AH3	I	200 Ω to GND	—
SD2_IMP_CAL_TX	Y1	I	100 Ω to GND	—
SD2_PLL_TPA	AH1	O	AVDD_SRDS2 ANALOG	17
No Connect Pins				
NC	C19, D7, D10, K13, L6, K9, B6, F12, J7, M19, M25, N19, N24, P19, R19, AB19, T12, W3, M12, W5, P12, T19, W1, W7, L13, U19, W4, V8, V9, V10, V11, V12, V13, V14, V15, V16, V17, V18, V19, W2, W6, W8, T11, U11, W12, W13, W14, W15, W16, W17, W18, W19, W27, V25, Y17, Y18, Y19, AA18, AA19, AB20, AB21, AB22, AB23, J9	—	—	—

Notes:

1. All multiplexed signals are listed only once and do not re-occur. For example, $\overline{\text{LCS5}}/\overline{\text{DMA\_REQ2}}$ is listed only once in the Local Bus Controller Interface section, and is not mentioned in the DMA section even though the pin also functions as $\overline{\text{DMA\_REQ2}}$.
2. Recommend a weak pull-up resistor (2–10 KΩ) be placed on this pin to OV_{DD}.
3. This pin must always be pulled high.
4. This pin is a reset configuration pin. It has a weak internal pull-up P-FET which is enabled only when the processor is in the reset state. This pull-up is designed such that it can be overpowered by an external 4.7-kΩ pull-down resistor. However, if the signal is intended to be high after reset, and if there is any device on the net which might pull down the value of the net at reset, then a pull-up or active driver is needed.
5. Treat these pins as no connects (NC) unless using debug address functionality.

Note that there is no default for this PLL ratio; these signals must be pulled to the desired values. Also note that the DDR data rate is the determining factor in selecting the CCB bus frequency, since the CCB frequency must equal the DDR data rate.

Table 60. CCB Clock Ratio

Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio	Binary Value of LA[28:31] Signals	CCB:SYSCLK Ratio
0000	16:1	1000	8:1
0001	Reserved	1001	9:1
0010	Reserved	1010	10:1
0011	3:1	1011	Reserved
0100	4:1	1100	12:1
0101	5:1	1101	Reserved
0110	6:1	1110	Reserved
0111	Reserved	1111	Reserved

19.3 e500 Core PLL Ratio

Table 61 describes the clock ratio between the e500 core complex bus (CCB) and the e500 core clock. This ratio is determined by the binary value of LBCTL, LALE, and LGPL2 at power up, as shown in Table 61.

Table 61. e500 Core to CCB Clock Ratio

Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core:CCB Clock Ratio	Binary Value of LBCTL, LALE, LGPL2 Signals	e500 core:CCB Clock Ratio
000	4:1	100	2:1
001	Reserved	101	5:2
010	Reserved	110	3:1
011	3:2	111	7:2

19.4 PCI Clocks

For specifications on the PCI_CLK, refer to the *PCI 2.2 Local Bus Specifications*.

The use of PCI_CLK is optional if SYSCLK is in the range of 33–66 MHz. If SYSCLK is outside this range then use of PCI_CLK is required as a separate PCI clock source, asynchronous with respect to SYSCLK.

20.3 Thermal Management Information

This section provides thermal management information for the flip chip plastic ball grid array (FC-PBGA) package for air-cooled applications. Proper thermal control design is primarily dependent on the system-level design—the heat sink, airflow, and thermal interface material. The MPC8533E implements several features designed to assist with thermal management, including the temperature diode. The temperature diode allows an external device to monitor the die temperature in order to detect excessive temperature conditions and alert the system; see Section 20.3.4, "Temperature Diode," for more information.

The recommended attachment method to the heat sink is illustrated in Figure 57. The heat sink should be attached to the printed-circuit board with the spring force centered over the die. This spring force should not exceed 10 pounds force (45 Newton).

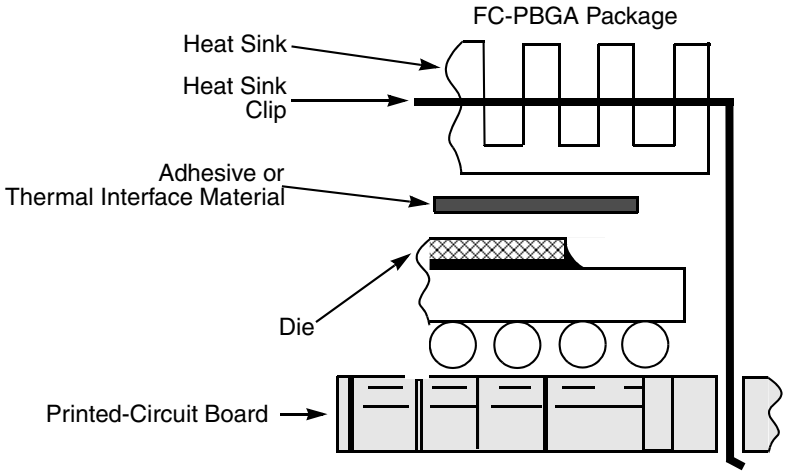

Figure 57. Package Exploded Cross-Sectional View with Several Heat Sink Options

The system board designer can choose between several types of heat sinks to place on the device. There are several commercially-available heat sinks from the following vendors:

Aavid Thermalloy603-224-9988
80 Commercial St.
Concord, NH 03301
Internet: www.aavidthermalloy.com

Advanced Thermal Solutions781-769-2800
89 Access Road #27.
Norwood, MA02062
Internet: www.qats.com

Alpha Novatech408-567-8082
473 Sapena Ct. #12
Santa Clara, CA 95054
Internet: www.alphanovatech.com

International Electronic Research Corporation (IERC)818-842-7277
413 North Moss St.
Burbank, CA 91502
Internet: www.ctscorp.com

Millennium Electronics (MEI)408-436-8770
Loroco Sites
671 East Brokaw Road
San Jose, CA 95112
Internet: www.mei-thermal.com

Tyco Electronics800-522-6752
Chip Coolers™
P.O. Box 3668
Harrisburg, PA 17105-3668
Internet: www.chipcoolers.com

Wakefield Engineering603-635-2800
33 Bridge St.
Pelham, NH 03076
Internet: www.wakefield.com

Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost. Several heat sinks offered by Aavid Thermalloy, Advanced Thermal Solutions, Alpha Novatech, IERC, Chip Coolers, Millennium Electronics, and Wakefield Engineering offer different heat sink-to-ambient thermal resistances, that will allow the MPC8533E to function in various environments.

20.3.1 Internal Package Conduction Resistance

For the packaging technology, shown in Table 65, the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-board thermal resistance

Note the following:

- AV_{DD}_SRDS should be a filtered version of SV_{DD}.
- Signals on the SerDes interface are fed from the XV_{DD} power plane.

21.3 Decoupling Recommendations

Due to large address and data buses, and high operating frequencies, the device can generate transient power surges and high frequency noise in its power supply, especially while driving large capacitive loads. This noise must be prevented from reaching other components in the MPC8533E system, and the device itself requires a clean, tightly regulated source of power. Therefore, it is recommended that the system designer place at least one decoupling capacitor at each V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} pin of the device. These decoupling capacitors should receive their power from separate V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD}; and GND power planes in the PCB, utilizing short low impedance traces to minimize inductance. Capacitors may be placed directly under the device using a standard escape pattern. Others may surround the part.

These capacitors should have a value of 0.01 or 0.1 µF. Only ceramic SMT (surface mount technology) capacitors should be used to minimize lead inductance, preferably 0402 or 0603 sizes.

In addition, it is recommended that there be several bulk storage capacitors distributed around the PCB, feeding the V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} planes, to enable quick recharging of the smaller chip capacitors. These bulk capacitors should have a low ESR (equivalent series resistance) rating to ensure the quick response time necessary. They should also be connected to the power and ground planes through two vias to minimize inductance. Suggested bulk capacitors—100–330 µF (AVX TPS tantalum or Sanyo OSCON). However, customers should work directly with their power regulator vendor for best values and types and quantity of bulk capacitors.

21.4 SerDes Block Power Supply Decoupling Recommendations

The SerDes block requires a clean, tightly regulated source of power (SV_{DD} and XV_{DD}) to ensure low jitter on transmit and reliable recovery of data in the receiver. An appropriate decoupling scheme is outlined below.

Only surface mount technology (SMT) capacitors should be used to minimize inductance. Connections from all capacitors to power and ground should be done with multiple vias to further reduce inductance.

- First, the board should have at least 10 × 10-nF SMT ceramic chip capacitors as close as possible to the supply balls of the device. Where the board has blind vias, these capacitors should be placed directly below the chip supply and ground connections. Where the board does not have blind vias, these capacitors should be placed in a ring around the device as close to the supply and ground connections as possible.
- Second, there should be a 1-µF ceramic chip capacitor on each side of the device. This should be done for all SerDes supplies.
- Third, between the device and any SerDes voltage regulator there should be a 10-µF, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a 100-µF, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

21.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. All unused active low inputs should be tied to V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD} as required. All unused active high inputs should be connected to GND. All NC (no connect) signals must remain unconnected. Power and ground connections must be made to all external V_{DD}, TV_{DD}, BV_{DD}, OV_{DD}, GV_{DD}, and LV_{DD}, and GND pins of the device.

21.6 Pull-Up and Pull-Down Resistor Requirements

The MPC8533E requires weak pull-up resistors (2–10 kΩ is recommended) on open drain type pins including I^2C pins and MPIC interrupt pins.

Correct operation of the JTAG interface requires configuration of a group of system control pins as demonstrated in Figure 65. Care must be taken to ensure that these pins are maintained at a valid deasserted state under normal operating conditions as most have asynchronous behavior and spurious assertion will give unpredictable results.

The following pins must NOT be pulled down during power-on reset: TSEC3_TXD[3], $\overline{\text{HRESET\_REQ}}$, TRIG_OUT/READY/$\overline{\text{QUIESCE}}$, MSRCID[2:4], ASLEEP. The $\overline{\text{DMA\_DACK}}$[0:1] and $\overline{\text{TEST\_SEL}}$ pins must be set to a proper state during POR configuration. Refer to the pinout listing table (Table 57) for more details. Refer to the *PCI 2.2 Local Bus Specifications,* for all pullups required for PCI.

21.7 Output Buffer DC Impedance

The MPC8533E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C). To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to OV_{DD} or GND. Then, the value of each resistor is varied until the pad voltage is $OV_{DD}/2$ (see Figure 63). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open) and R_P is trimmed until the voltage at the pad equals $OV_{DD}/2$. R_P then becomes the

resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N) \div 2$.

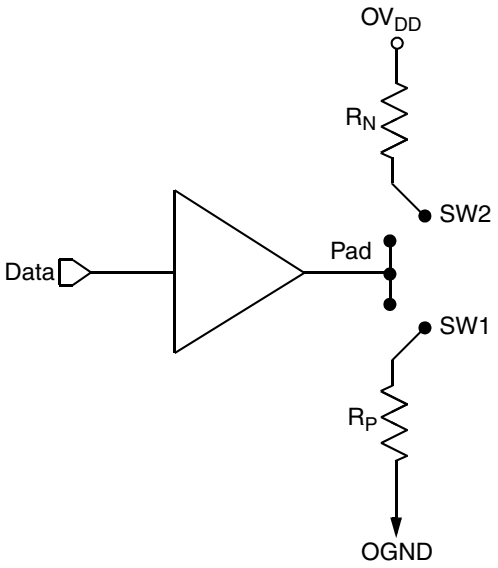

Figure 63. Driver Impedance Measurement

Table 68 summarizes the signal impedance targets. The driver impedances are targeted at minimum V_{DD}, nominal OV_{DD}, 90°C.

Table 68. Impedance Characteristics

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI	DDR DRAM	Symbol	Unit
R_N	43 Target	25 Target	20 Target	Z_0	W
R_P	43 Target	25 Target	20 Target	Z_0	W

Note: Nominal supply voltages. See Table 1.

21.8 Configuration Pin Muxing

The MPC8533E provides the user with power-on configuration options which can be set through the use of external pull-up or pull-down resistors of 4.7 kΩ on certain output pins (see customer visible configuration pins). These pins are generally used as output only pins in normal operation.

While $\overline{\text{HRESET}}$ is asserted however, these pins are treated as inputs. The value presented on these pins while $\overline{\text{HRESET}}$ is asserted, is latched when $\overline{\text{HRESET}}$ deasserts, at which time the input receiver is disabled and the I/O circuit takes on its normal function. Most of these sampled configuration pins are equipped with an on-chip gated resistor of approximately 20 kΩ. This value should permit the 4.7-kΩ resistor to pull the configuration pin to a valid logic low level. The pull-up resistor is enabled only during $\overline{\text{HRESET}}$ (and for platform /system clocks after $\overline{\text{HRESET}}$ deassertion to ensure capture of the reset value). When the input receiver is disabled the pull-up is also, thus allowing functional operation of the pin as an output with minimal signal quality or delay disruption. The default value for all configuration bits treated this way has

23 Document Revision History

This table provides a revision history for the MPC8533E hardware specification.

Table 71. MPC8533E Document Revision History

Revision	Date	Substantive Change(s)
8	09/2015	• In Table 10 and Table 12, removed the output leakage current rows and removed table note 4.
7	06/2014	• In Table 70, “Device Nomenclature,” added full Pb-free part code. • In Table 70, “Device Nomenclature,” added footnotes 3 and 4.
6	05/2011	• Updated the value of t_{JTKLDX} to 2.5 ns from 4ns in Table 45.
5	01/2011	• Updated Table 70.
4	09/2010	• Modified local bus information in Section 1.1, “Key Features,” to show max local bus frequency as 133 MHz. • Added footnote 28 to Table 57. • Updated solder-ball parameter in Table 56.
3	11/2009	• Update Section 20.3.4, “Temperature Diode,” • Update Table 56 Package Parameters from 95.5%sn to 96.5%sn
2	01/2009	• • Update power number table to include 1067 MHz/533 MHz power numbers. • Remove Part number tables from Hardware spec. The part numbers are available on Freescale web site product page. • Removed I/O power numbers from the Hardware spec. and added the table to bring-up guide applacation note • Updated RX_CLK duty cycle min, and max value to meet the industry standard GMII duty cycle. • In Table 35, removed note 1 and renumbered remaining note. • Update paragraph Section 21.3, “Decoupling Recommendations • Update t_{DDKHMP}, t_{DDKHME} in Table 18 • Update Figure 5 DDR Output Timing Diagram
1	06/2008	Update in Table 18 DDR SDRAM Output AC Timing Specifications tMCK Max value Improvement to Section 16, “High-Speed Serial Interfaces (HSSI) Update Figure 55 Mechanical Dimensions Update in Table 43 Local Bus General Timing Parameters—PLL Bypassed
0	04/2008	Initial release.